

ROHS COMPLIANT

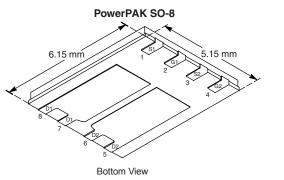
HALOGEN

FREE Available

Vishay Siliconix

Dual P-Channel 30-V (D-S) MOSFET

PRODUCT SUMMARY					
V _{DS} (V)	R_{DS(on)} (Ω)	I _D (A)	Q _g (Typ.)		
- 30	0.020 at V_{GS} = - 10 V	- 10.9	49		
	0.031 at V_{GS} = - 4.5 V	- 8.8	45		



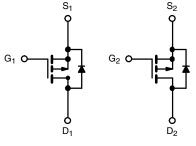
Ordering Information: Si7945DP-T1-E3 (Lead (Pb)-free) Si7945DP-T1-GE3 (Lead (Pb)-free and Halogen-free)

FEATURES

- Halogen-free According to IEC 61249-2-21
 Available
- TrenchFET[®] Power MOSFETs
- New Low Thermal Resistance PowerPAK[®] Package with Low 1.07 mm Profile

APPLICATIONS

- · Battery and Load Switching
 - Notebook PCs
 - Game Systems
 - Set-Top Box



P-Channel MOSFET P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS	T _A = 25 °C, unles	ss otherwise n	oted		
Parameter		Symbol	10 s	Steady State	Unit
Drain-Source Voltage		V _{DS}	- 30		V
Gate-Source Voltage		V _{GS}	± 20		
Continuous Drain Current (T _J = 150 °C) ^a	T _A = 25 °C	I _D	- 10.9	- 7.0	
Continuous Drain Current $(T_J = 150^{\circ} \text{ C})^{\circ}$	T _A = 70 °C		- 8.7	- 5.6	А
Pulsed Drain Current		I _{DM}	- 30		A
Continuous Source Current (Diode Conduction) ^a		۱ _S	- 2.9	- 1.2	
Mauimum Daucar Diagingtignal	T _A = 25 °C	P _D	3.5	1.4	W
Maximum Power Dissipation ^a	T _A = 70 °C		2.2	0.9	vv
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150		°C
Soldering Recommendations (Peak Temperature) ^{b, c}			260		

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Mauinum lunation to Anchienta	t ≤ 10 s	R _{thJA}	26	35	
Maximum Junction-to-Ambient ^a	Steady State		60	85	°C/W
Maximum Junction-to-Case (Drain)	Steady State	R _{thJC}	2.5	3.1	

Notes:

a. Surface Mounted on 1" x 1" FR4 board.

b. See Solder Profile (<u>www.vishay.com/ppg?73257</u>). The PowerPAK SO-8 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.

c. Rework Conditions: manual soldering with a soldering iron is not recommended for leadless components.

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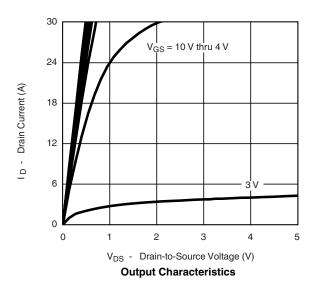
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static		·					
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = -250 \ \mu A$	- 1.0		- 3.0	V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 V, V_{GS} = \pm 20 V$			± 100	nA	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = - 30 V, V _{GS} = 0 V			- 1	μA	
		$V_{DS} = -30$ V, $V_{GS} = 0$ V, $T_{J} = 55$ °C			- 5		
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \leq$ - 5 V, V_{GS} = - 10 V	- 30			А	
	R _{DS(on)}	V _{GS} = - 10 V, I _D = - 10.9 A		0.016	0.020	Ω	
Drain-Source On-State Resistance ^a		V _{GS} = - 4.5 V, I _D = - 8.8 A		0.025	0.031		
Forward Transconductance ^a	9 _{fs}	V _{DS} = - 15 V, I _D = - 10.9 A		26		S	
Diode Forward Voltage ^a	V _{SD}	I _S = - 2.9 A, V _{GS} = 0 V		- 0.8	- 1.2	V	
Dynamic ^b		•		•			
Total Gate Charge	Qg			49	74		
Gate-Source Charge	Q _{gs}	$V_{DS} = -15 \text{ V}, V_{GS} = -10 \text{ V}, I_{D} = -10.9 \text{ A}$		7.3		nC	
Gate-Drain Charge	Q _{gd}			13			
Turn-On Delay Time	t _{d(on)}			15	25		
Rise Time	t _r	V_{DD} = - 15 V, R_L = 15 Ω		15	25	ns	
Turn-Off Delay Time	t _{d(off)}	${\rm I}_{\rm D}\cong$ - 1 A, ${\rm V}_{\rm GEN}$ = - 10 V, ${\rm R}_{\rm g}$ = 6 Ω		130	200		
Fall Time	t _f			80	120		
Source-Drain Reverse Recovery Time	t _{rr}	I _F = - 2.9 A, dl/dt = 100 A/μs		85	130		

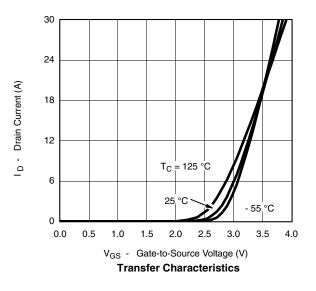
Notes:

a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %. b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



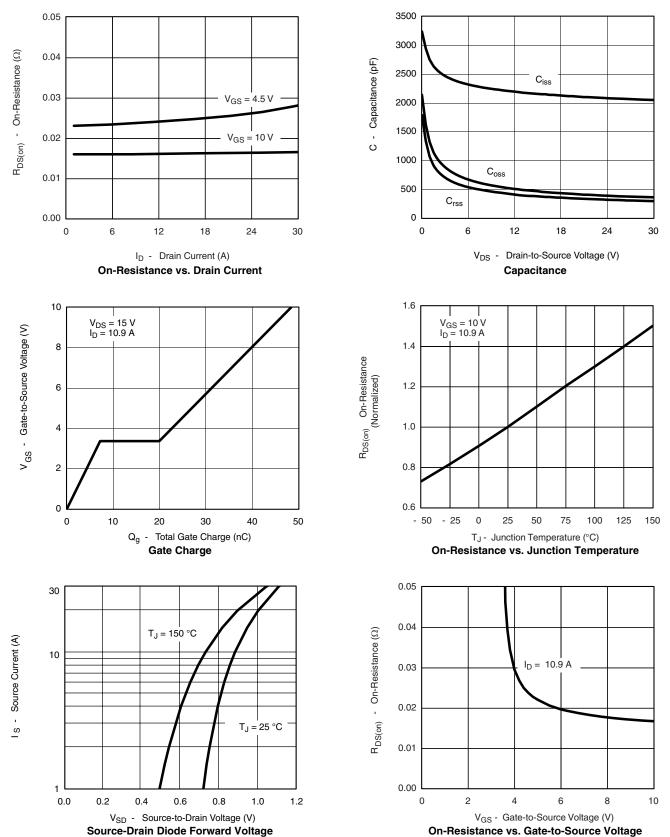




Si7945DP

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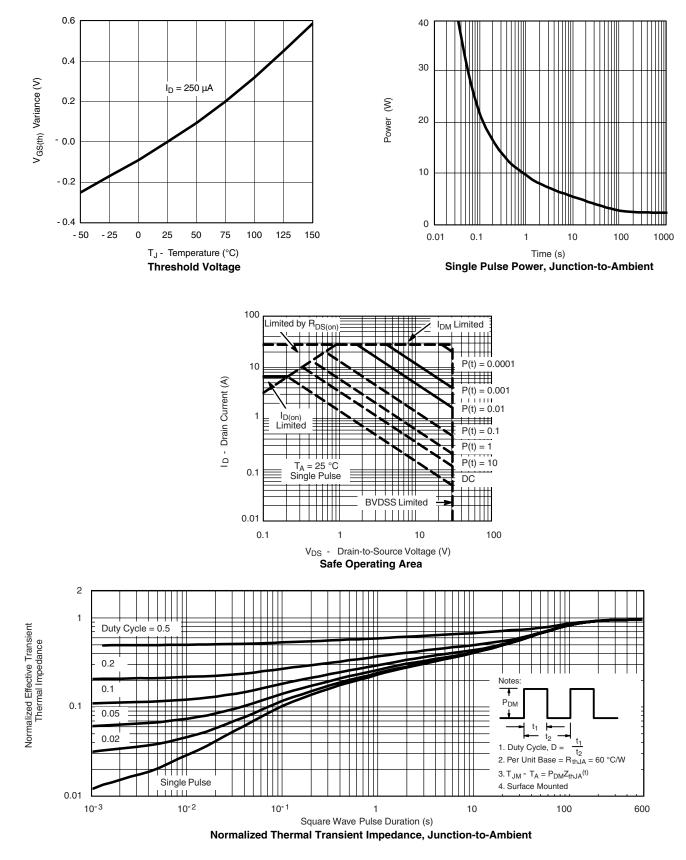
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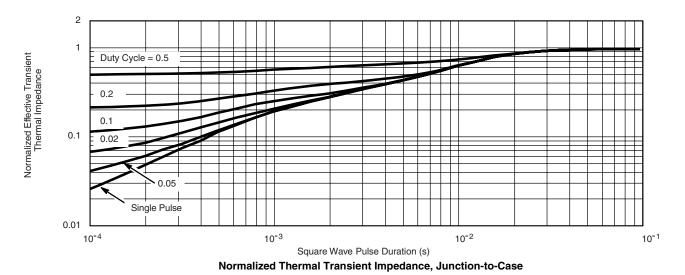




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TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see <u>www.vishay.com/ppg?72090</u>.



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